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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

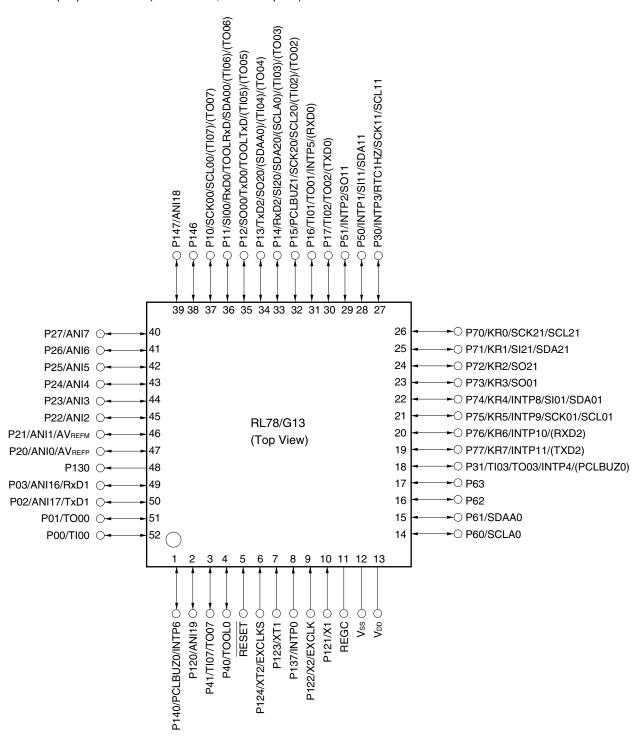
Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100fadfp-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1.3.10 52-pin products

• 52-pin plastic LQFP (10 × 10 mm, 0.65 mm pitch)



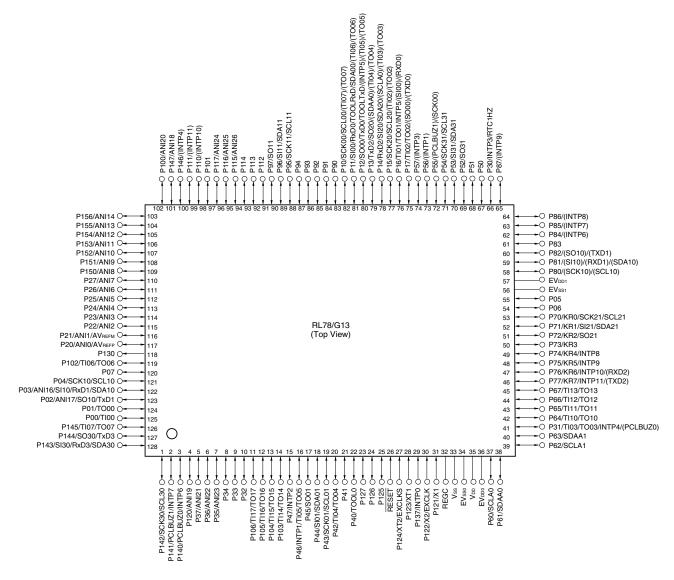
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.3.14 128-pin products

• 128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)



Cautions 1. Make EVsso, EVss1 pins the same potential as Vss pin.

- 2. Make VDD pin the potential that is higher than EVDDD, EVDDD pins (EVDDD = EVDDD).
- 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the Vss, EVss₀ and EVss₁ pins to separate ground lines.
- 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.4 Pin Identification

ANI0 to ANI14,		REGC:	Regulator capacitance
ANI16 to ANI26:	Analog input	RESET:	Reset
AVREFM:	A/D converter reference	RTC1HZ:	Real-time clock correction clock
	potential (- side) input		(1 Hz) output
AVREFP:	A/D converter reference	RxD0 to RxD3:	Receive data
	potential (+ side) input	SCK00, SCK01, SCK10,	
EVDD0, EVDD1:	Power supply for port	SCK11, SCK20, SCK21,	
EVsso, EVss1:	Ground for port	SCLA0, SCLA1:	Serial clock input/output
EXCLK:	External clock input (Main	SCLA0, SCLA1, SCL00,	
	system clock)	SCL01, SCL10, SCL11,	
EXCLKS:	External clock input	SCL20,SCL21, SCL30,	
	(Subsystem clock)	SCL31:	Serial clock output
INTP0 to INTP11:	Interrupt request from	SDAA0, SDAA1, SDA00	,
	peripheral	SDA01,SDA10, SDA11,	
KR0 to KR7:	Key return	SDA20,SDA21, SDA30,	
P00 to P07:	Port 0	SDA31:	Serial data input/output
P10 to P17:	Port 1	SI00, SI01, SI10, SI11,	
P20 to P27:	Port 2	SI20, SI21, SI30, SI31:	Serial data input
P30 to P37:	Port 3	SO00, SO01, SO10,	
P40 to P47:	Port 4	SO11, SO20, SO21,	
P50 to P57:	Port 5	SO30, SO31:	Serial data output
P60 to P67:	Port 6	TI00 to TI07,	
P70 to P77:	Port 7	TI10 to TI17:	Timer input
P80 to P87:	Port 8	TO00 to TO07,	
P90 to P97:	Port 9	TO10 to TO17:	Timer output
P100 to P106:	Port 10	TOOL0:	Data input/output for tool
P110 to P117:	Port 11	TOOLRxD, TOOLTxD:	Data input/output for external device
P120 to P127:	Port 12	TxD0 to TxD3:	Transmit data
P130, P137:	Port 13	V _{DD} :	Power supply
P140 to P147:	Port 14	Vss:	Ground
P150 to P156:	Port 15	X1, X2:	Crystal oscillator (main system clock)
PCLBUZ0, PCLBUZ1	: Programmable clock	XT1, XT2:	Crystal oscillator (subsystem clock)
	output/buzzer output		

3. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see **6.9.3 Operation as multiple PWM output function** in the RL78/G13 User's Manual).

4. When setting to PIOR = 1

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Iter	m	20-	nin	24-	nin	25-	nin	30-	pin	32	-pin	36	pin
itoi											İ		i
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Clock output/buzze	er output	-	=		1		1		2		2		2
		2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation)											
8/10-bit resolution	A/D converter	6 chanr	nels	6 chanr	nels	6 chanr	nels	8 chanı	nels	8 chan	nels	8 chan	nels
Serial interface		[20-pin,	24-pin,	25-pin p	roducts]								
		• CSI:	1 chann	el/simplif	ied I ² C:	1 channe	el/UART	: 1 chanr	nel				
		• CSI:	1 chann	el/simplif	ied I ² C:	1 channe	el/UART	: 1 chanr	nel				
		[30-pin,	32-pin	products]]								
		• CSI:	1 chann	el/simplif el/simplif	ied I ² C:	1 channe	el/UART	: 1 chanr	nel				
				el/simplif	fied I ² C:	1 channe	el/UART	(UART s	supportir	ng LIN-b	us): 1 ch	nannel	
		[36-pin											
		1		el/simplif el/simplif									
1				els/simpli						rting LIN	-bus): 1	channel	
ſ	I ² C bus	-	=	1 chanr		1 chanr		1 chanı		1 chan		1 chan	nel
Multiplier and divide accumulator	er/multiply-	 16 bits × 16 bits = 32 bits (Unsigned or signed) 32 bits ÷ 32 bits = 32 bits (Unsigned) 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 											
DMA controller		2 chanr	nels										
Vectored interrupt	Internal	2	3	2	24	2	<u>!</u> 4	2	27	2	27	2	27
sources	External	;	3	ļ	5		5		6		6		6
Key interrupt	External												
Reset													
		InterrInterrInterrInterrInterr	nal reset nal reset nal reset nal reset nal reset	SET pin by watch by power by volta by illega by RAM by illega	er-on-res ge detec al instruc parity e	et ctor tion exec rror		e					
Power-on-reset circ	puit	InterrInterrInterrInterrInterrInterrInterrPower	nal reset nal reset nal reset nal reset nal reset er-on-res	by watch by power by volta by illega by RAM by illega	er-on-res ge detect al instruct parity e al-memodes 51 V (T	et stor stor tion exec rror ry access		0					
Power-on-reset circ	cuit	InterrInterrInterrInterrInterrInterrInterrPower	nal reset nal reset nal reset nal reset nal reset nal reset er-on-reser er-down-	by watch by power by volta by illega by RAM by illega set: 1 reset: 1	er-on-res ge detectal instruction parity et al-memorial.51 V (Tours) (et stor stor tion exec rror ry access	s 14 stage	es)					
		Interr Interr Interr Interr Interr Interr Interr Powe	nal reset nal reset nal reset nal reset nal reset nal reset er-on-reser-down- g edge: g edge	by watch by power by volta by illega by RAM by illega set: 1 reset: 1	er-on-res ge detectal instruction parity et al-memorial.51 V (Tours) (et ctor tion exec rror ry access YP.) YP.)	s 14 stage	es)					
Voltage detector	ction	Interresistant Interr	nal reset er-on-reser-down- g edge: g edge d	by watch by power by volta by illega by RAM by illega set: 1 reset: 1	er-on-res ge detect al instruct parity e al-memon .51 V (T .50 V (T .67 V to	set stor rich execution ex	s 14 stage	es)					
Voltage detector On-chip debug fund	ction	 Interr Interr Interr Interr Interr Interr Powe Powe Rising Fallin Provide 	nal reset er-on-reser down- g edge: g edge d	by watch by power by volta by illega by RAM by illega set: 1 rreset: 1	er-on-res ge detect al instruct parity e al-memon .51 V (T .50 V (T .67 V to .63 V to	set stor return execution exec	s 14 stage	es)					
Voltage detector On-chip debug fund	ction	 Interr Interr Interr Interr Interr Interr Interr Powe Powe Rising Fallin Provide V_{DD} = 1 V_{DD} = 2. 	nal reset er-on-reser er-down- g edge g edge d .6 to 5.5	by watch by power by volta by illegate by RAM by illegate by illeg	er-on-res ge detect al instruct parity e al-memor .51 V (T .50 V (T .63 V to .63 V to	set stor rich execution ex	s 14 stage 14 stage	es)	applica	tions)			

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

 The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13 User's Manual).

(2/2)

lla		80-pin 100-pin			(2/2)								
Ite	em				100-pin		8-pin						
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx						
Clock output/buzz	er output		2 2 2										
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz											
		(Main system clock: fmain = 20 MHz operation)											
		• 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: fsub = 32.768 kHz operation)											
8/10-bit resolution	A/D converter	17 channels	710011. 100B — 0E.7	20 channels	<u>'</u>	26 channels							
Serial interface	TAB CONVOICE		, 128-pin produc			20 onamoio							
ocha interiace				: 2 channels/UAR	T: 1 channal								
			•	: 2 channels/UAR									
			•	: 2 channels/UAR		ting LIN-bus): 1 o	channel						
		CSI: 2 channel	els/simplified I ² C	2 channels/UAR	T: 1 channel								
	I ² C bus	2 channels		2 channels		2 channels							
Multiplier and divid	der/multiply-	• 16 bits × 16 bi	ts = 32 bits (Uns	igned or signed)									
accumulator		• 32 bits ÷ 32 bits = 32 bits (Unsigned)											
		• 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)											
DMA controller		4 channels	4 channels										
Vectored	Internal	3	37	3	37		41						
interrupt sources	External	1	13	1	3		13						
Key interrupt			8	;	8		8						
Reset		Reset by RES	SET pin										
			by watchdog tim										
			by power-on-res										
			by voltage detec	ctor ction execution Note									
			by RAM parity e										
		Internal reset by Hawi party error Internal reset by illegal-memory access											
Power-on-reset ci	rcuit	Power-on-res	et: 1.51 V (TY	′P.)									
		Power-down-reset: 1.50 V (TYP.)											
Voltage detector		Rising edge :	1.67 V to 4	1.06 V (14 stages))								
		Falling edge :	1.63 V to 3	3.98 V (14 stages)									
On-chip debug fur	nction	Provided											
Power supply volt	age	$V_{DD} = 1.6 \text{ to } 5.5$	$V (T_A = -40 \text{ to } +8$	35°C)									
		$V_{DD} = 2.4 \text{ to } 5.5$	$V (T_A = -40 \text{ to } +1)$	05°C)									
Operating ambien	t temperature	$T_A = 40 \text{ to } +85^\circ$	C (A: Consumer	applications, D: Ir	ndustrial applicat	ions)							
		$T_A = 40 \text{ to } +105$	°C (G: Industrial	applications)			$T_A = 40 \text{ to } +105^{\circ}\text{C}$ (G: Industrial applications)						



Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (4/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -10.0 mA	EV _{DD0} –			V
		to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $I_{\text{OH1}} = -3.0 \text{ mA}$	EV _{DD0} – 0.7			V
	P117, P120, P125 to P127, P130, P140 to P147	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ loh1 = -2.0 mA	EV _{DD0} – 0.6			V	
			$1.8 \ V \le EV_{DD0} \le 5.5 \ V,$ Iон1 = $-1.5 \ mA$	EV _{DD0} – 0.5			V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ Iон1 = -1.0 mA	EV _{DD0} – 0.5			V
	V _{OH2}	P20 to P27, P150 to P156	1.6 V \leq V _{DD} \leq 5.5 V, I _{OH2} = $-100~\mu$ A	V _{DD} – 0.5			V
Output voltage, VoL1	V _{OL1}	P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 20~mA$			1.3	V
			$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 8.5~mA$			0.7	V
			$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$ $I_{\text{OL1}} = 3.0~\text{mA}$			0.6	V
			$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$ $I_{\text{OL1}} = 1.5~\text{mA}$			0.4	V
			$1.8~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 0.6~mA$			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ $\text{IoL1} = 0.3 \text{ mA}$			0.4	V
	V _{OL2}	P20 to P27, P150 to P156	1.6 V \leq V _{DD} \leq 5.5 V, I _{OL2} = 400 μ A			0.4	V
	Vol3	P60 to P63	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{Iol3} = 15.0 \text{ mA}$			2.0	V
			$4.0~V \le EV_{DD0} \le 5.5~V,$ $I_{OL3} = 5.0~mA$			0.4	V
			$2.7~\textrm{V} \leq \textrm{EV}_\textrm{DD0} \leq 5.5~\textrm{V},$ $\textrm{Iol3} = 3.0~\textrm{mA}$			0.4	V
			$1.8~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 2.0~mA$			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ $10 \text{L3} = 1.0 \text{ mA}$			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVSSO, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V \leq VDD \leq 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 16 MHz

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 8 MHz LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - **3.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz

 $2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 16 MHz

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ @1 MHz to 8 MHz LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ @1 MHz to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fih: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

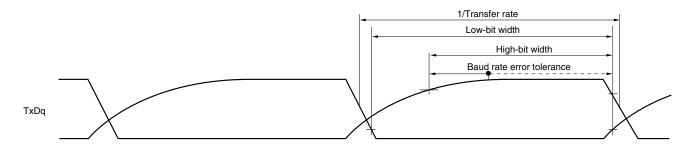
Parameter	Symbol	C	Conditions	HS (high main)	•	LS (low main)	•	LV (low- main)	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 ≥ 4/fс∟к	$2.7~V \leq EV_{DD0} \leq 5.5$ V	125		500		1000		ns
			$2.4~V \leq EV_{DD0} \leq 5.5$ V	250		500		1000		ns
			$1.8~V \leq EV_{DD0} \leq 5.5$ V	500		500		1000		ns
			$1.7~V \leq EV_{DD0} \leq 5.5$ V	1000		1000		1000		ns
			$1.6~V \le EV_{DD0} \le 5.5$ V	_		1000		1000		ns
SCKp high-/low-level width	tкн1, tкL1	$4.0~\text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5~\text{V}$		tксу1/2 — 12		tксу1/2 — 50		tксү1/2 — 50		ns
		$2.7~\text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5~\text{V}$		tксу1/2 — 18		tксу1/2 — 50		tксү1/2 — 50		ns
		$2.4~V \leq EV_{DD0} \leq 5.5~V$		tксү1/2 – 38		tксү1/2 – 50		tксү1/2 – 50		ns
		1.8 V ≤ EVD	₀₀ ≤ 5.5 V	tксү1/2 — 50		tксу1/2 — 50		tксү1/2 — 50		ns
		1.7 V ≤ EVD	₀₀ ≤ 5.5 V	tксу1/2 — 100		tксу1/2 — 100		tксу1/2 — 100		ns
		1.6 V ≤ EV _D	₀₀ ≤ 5.5 V	_		tксу1/2 — 100		tксу1/2 — 100		ns
SIp setup time	tsıĸı	4.0 V ≤ EV _{DI}	00 ≤ 5.5 V	44		110		110		ns
(to SCKp↑)		2.7 V ≤ EV _{DI}	00 ≤ 5.5 V	44		110		110		ns
		2.4 V ≤ EV _{DI}	00 ≤ 5.5 V	75		110		110		ns
		1.8 V ≤ EV _{DI}	oo ≤ 5.5 V	110		110		110		ns
		1.7 V ≤ EV _{DI}	oo ≤ 5.5 V	220		220		220		ns
		1.6 V ≤ EV _{DI}	00 ≤ 5.5 V	_		220		220		ns
SIp hold time	t _{KSI1}	1.7 V ≤ EV _{DI}	00 ≤ 5.5 V	19		19		19		ns
(from SCKp↑) Note 2		1.6 V ≤ EV _{DI}	00 ≤ 5.5 V	_		19		19		ns
Delay time from SCKp↓ to SOp	tkso1	$1.7 \text{ V} \le \text{EV}_{DI}$ $C = 30 \text{ pF}^{\text{Note}}$			25		25		25	ns
output Note 3		$1.6 \text{ V} \leq \text{EV}_{DI}$ $C = 30 \text{ pF}^{\text{Note}}$			_		25		25	ns

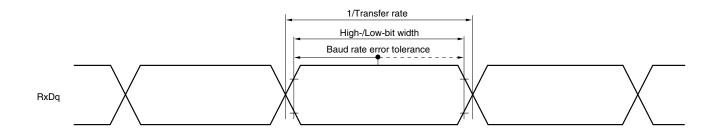
Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode bit width (during communication at different potential) (reference)





- $\begin{tabular}{ll} \begin{tabular}{ll} \bf R_b[\Omega]: Communication line (TxDq) pull-up resistance, \\ C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage \\ \end{tabular}$
 - 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)

(Ta = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (high main)	•	,	/-speed Mode	LV (low main)	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	1/fмск + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	1/fмск + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	1/fмск + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	1/fmck + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ &1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \\ &C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{aligned} $	1/fмск + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
Data hold time (transmission)	thd:dat	$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{aligned} &2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	0	355	0	355	0	355	ns
		$ \begin{aligned} &2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	0	355	0	355	0	355	ns
		$ \begin{split} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{split} $	0	405	0	405	0	405	ns

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

- 2. Use it with $EV_{DD0} \ge V_b$.
- 3. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)



(3) Peripheral Functions (Common to all products)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	FIL Note 1				0.20		μΑ
RTC operating current	IRTC Notes 1, 2, 3				0.02		μΑ
12-bit interval timer operating current	IIT Notes 1, 2, 4				0.02		μА
Watchdog timer operating current	WDT Notes 1, 2, 5	fı∟ = 15 kHz			0.22		μΑ
A/D converter operating	ADC Notes 1, 6	When conversion at maximum	Normal mode, AVREFP = VDD = 5.0 V		1.3	1.7	mA
current		speed	Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	IADREF Note 1				75.0		μΑ
Temperature sensor operating current	ITMPS Note 1				75.0		μA
LVD operating current	ILVD Notes 1, 7				0.08		μА
Self programming operating current	FSP Notes 1, 9				2.50	12.20	mA
BGO operating current	BGO Notes 1, 8				2.50	12.20	mA
SNOOZE	Isnoz	ADC operation	The mode is performed Note 10		0.50	1.10	mA
operating current	Note 1		The A/D conversion operations are performed, Loe voltage mode, AVREFP = VDD = 3.0 V		1.20	2.04	mA
		CSI/UART operation	on		0.70	1.54	mA

Notes 1. Current flowing to the VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed onchip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- **5.** Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates.



5. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq EV_{DD0} < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

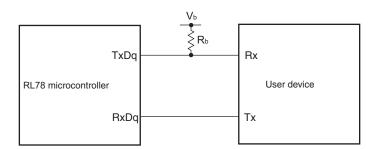
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{1.5}{V_b})}\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

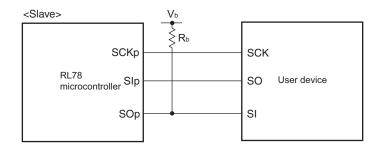
UART mode connection diagram (during communication at different potential)



- Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



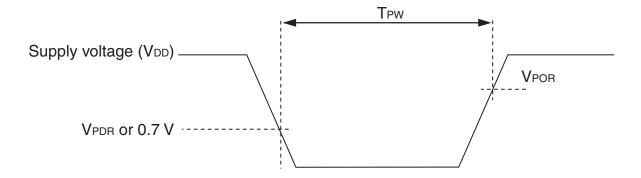
- **Remarks 1.** R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 00, 01, 02,
 - 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

3.6.3 POR circuit characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	POR Power supply rise time		1.51	1.57	V
	V _{PDR}	Power supply fall time	1.44	1.50	1.56	V
Minimum pulse width	T _{PW}		300			μS

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



R5F100GAANA, R5F100GCANA, R5F100GDANA, R5F100GEANA, R5F100GFANA, R5F100GHANA, R5F100GHANA, R5F100GHANA, R5F100GKANA, R5F100GKANA, R5F100GKANA

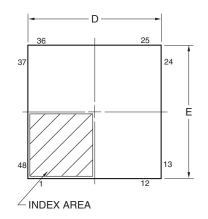
R5F101GAANA, R5F101GCANA, R5F101GDANA, R5F101GEANA, R5F101GFANA, R5F101GHANA, R5F101GHANA, R5F101GHANA, R5F101GKANA, R5F101GKANA, R5F101GLANA

R5F100GADNA, R5F100GCDNA, R5F100GDDNA, R5F100GEDNA, R5F100GFDNA, R5F100GDNA, R5F100GHDNA, R5F100GJDNA, R5F100GKDNA, R5F100GLDNA

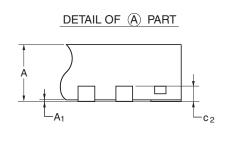
R5F101GADNA, R5F101GCDNA, R5F101GDDNA, R5F101GEDNA, R5F101GFDNA, R5F101GGDNA, R5F101GHDNA, R5F101GJDNA, R5F101GKDNA, R5F101GLDNA

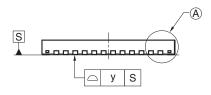
R5F100GAGNA, R5F100GCGNA, R5F100GDGNA, R5F100GEGNA, R5F100GFGNA, R5F100GHGNA, R5F100GJGNA

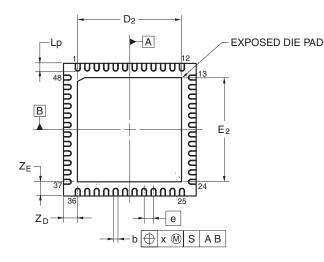
JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PJN-A P48K8-50-5B4-6	0.13











Referance	Dimens	sion in Mil	limeters
Symbol	Min	Nom	Max
D	6.95	7.00	7.05
Е	6.95	7.00	7.05
А			0.80
A ₁	0.00		
b	0.18	0.25	0.30
е		0.50	
Lp	0.30	0.40	0.50
Х			0.05
у			0.05
Z _D		0.75	
Z _E		0.75	
C ₂	0.15	0.20	0.25
D ₂		5.50	_
E ₂	_	5.50	_

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4.11 64-pin Products

R5F100LCAFA, R5F100LDAFA, R5F100LEAFA, R5F100LFAFA, R5F100LGAFA, R5F100LHAFA, R5F100LJAFA, R5F100LKAFA, R5F100LLAFA

R5F101LCAFA, R5F101LDAFA, R5F101LEAFA, R5F101LFAFA, R5F101LGAFA, R5F101LHAFA, R5F101LJAFA, R5F101LKAFA, R5F101LLAFA

R5F100LCDFA, R5F100LDDFA, R5F100LEDFA, R5F100LFDFA, R5F100LGDFA, R5F100LHDFA, R5F100LJDFA, R5F100LKDFA, R5F100LLDFA

R5F101LCDFA, R5F101LDDFA, R5F101LEDFA, R5F101LFDFA, R5F101LGDFA, R5F101LHDFA, R5F101LJDFA, R5F101LKDFA, R5F101LLDFA

Previous Code

MASS (TYP.) [g]

R5F100LCGFA, R5F100LDGFA, R5F100LEGFA, R5F100LFGFA, R5F100LGGFA, R5F100LHGFA, R5F100LJGFA

RENESAS Code

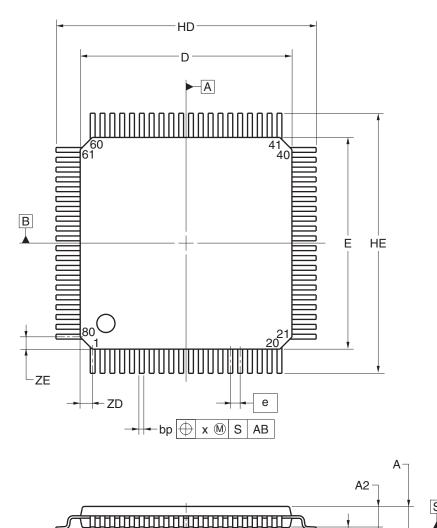
JEITA Package Code

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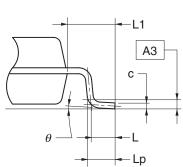
4.12 80-pin Products

R5F100MFAFA, R5F100MGAFA, R5F100MHAFA, R5F100MJAFA, R5F100MKAFA, R5F100MLAFA R5F101MFAFA, R5F101MGAFA, R5F101MHAFA, R5F101MJAFA, R5F101MKAFA, R5F101MLAFA R5F100MFDFA, R5F100MGDFA, R5F100MHDFA, R5F100MJDFA, R5F100MKDFA, R5F101MLDFA R5F101MFDFA, R5F101MGDFA, R5F101MHDFA, R5F101MJDFA, R5F101MKDFA, R5F101MLDFA R5F100MFGFA, R5F100MGGFA, R5F100MHGFA, R5F100MJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69



S



detail of lead end

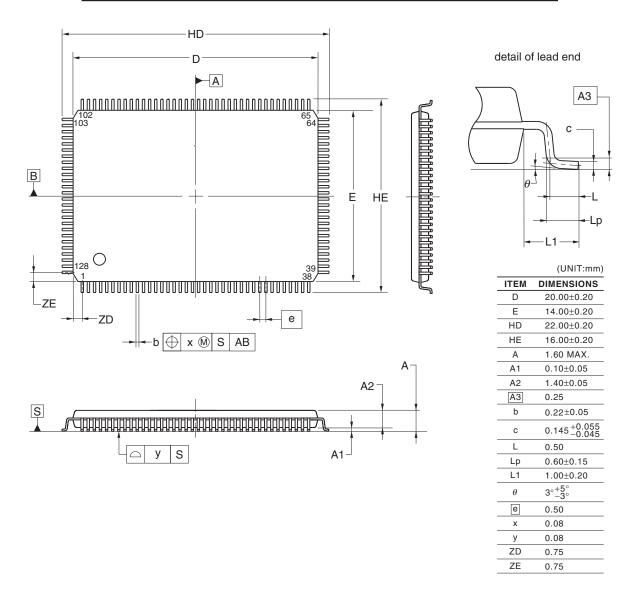
Referance Symbol	Dimension in Millimeters			
	Min	Nom	Max	
D	13.80	14.00	14.20	
Е	13.80	14.00	14.20	
HD	17.00	17.20	17.40	
HE	17.00	17.20	17.40	
Α			1.70	
A1	0.05	0.125	0.20	
A2	1.35	1.40	1.45	
A3		0.25		
bp	0.26	0.32	0.38	
С	0.10	0.145	0.20	
L		0.80		
Lp	0.736	0.886	1.036	
L1	1.40	1.60	1.80	
θ	0°	3°	8°	
е		0.65		
х			0.13	
У			0.10	
ZD		0.825		
ZE		0.825		

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4.14 128-pin Products

R5F100SHAFB, R5F100SJAFB, R5F100SKAFB, R5F100SLAFB R5F101SHAFB, R5F101SJAFB, R5F101SKAFB, R5F101SLAFB R5F100SHDFB, R5F100SJDFB, R5F100SKDFB, R5F100SLDFB R5F101SHDFB, R5F101SJDFB, R5F101SKDFB, R5F101SLDFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP128-14x20-0.50	PLQP0128KD-A	P128GF-50-GBP-1	0.92



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NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE: Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.